

SCAN182245A Non-Inverting Transceiver with 25Ω Series Resistor Outputs

General Description

The SCAN182245A is a high performance BiCMOS bidirectional line driver featuring separate data inputs organized into dual 9-bit bytes with byte-oriented output enable and direction control signals. This device is compliant with IEEE 1149.1 Standard Test Access Port and Boundary Scan Architecture with the incorporation of the defined boundary-scan test logic and test access port consisting of Test Data Input (TDI), Test Data Out (TDO), Test Mode Select (TMS), and Test Clock (TCK).

Features

- High performance BiCMOS technology
- 25Ω series resistors in outputs eliminate the need for external terminating resistors
- Dual output enable control signals
- TRI-STATE® outputs for bus-oriented applications
- 25 mil pitch SSOP (Shrink Small Outline Package)
- IEEE 1149.1 (JTAG) Compliant
- Includes CLAMP, IDCODE and HIGHZ instructions
- Additional instructions SAMPLE-IN, SAMPLE-OUT and EXTEST-OUT
- Power Up TRI-STATE for hot insert
- Member of National's SCAN Products

Connection Diagram

		-
TMS —	1 5	6 — TDI
в1 ₀ —	2 5	5 A 1 ₀
DIR 1 —	3 5	4 G1
в1 ₁ —	4 5	3 A 11
в1 ₂ —	5 5	2 A12
gnd 🗕	6 5	1 GND
B13 —	7 5	0 A 13
в1 ₄ —	8 4	9 A 1 ₄
v _{cc} —	9 4	8 - V _{CC}
B15 —	10 4	7 🗕 A 1 ₅
B1 ₆ —	11 4	6 A 1 ₆
GND —	12 4	5 — GND
B1 ₇ —	13 4	4 A 17
B1 ₈ —	14 4	3 A 1 ₈
82 ₀ —	15 4	2 A20
B2 ₁ —	16 4	1 A21
GND -	17 4	0 GND
в2 ₂ —	18 3	9 A22
B23 -	19 3	8 A23
v _{cc} —	20 3	V _{CC}
B2 ₄ —	21 3	6 A24
в2 ₅ —	22 3	5 A2 ₅
gnd —	23 3	4 GND
B2 ₆ —	24 3	3 A2 ₆
B2 ₇ —	25 3	2 A27
DIR2 -	26 3	1 - G2
в2 ₈ —	27 3	0 A28
TDO —	28 2	9 — тск
l		TL/F/11657-1
I-STATE® is a registered trade	mark of National Sem	conductor Corporation.

Pin Names	Description
A1 ₍₀₋₈₎	Side A1 Inputs or TRI-STATE Outputs
B1 ₍₀₋₈₎	Side B1 Inputs or TRI-STATE Outputs
A1 ₍₀₋₈₎ B1 ₍₀₋₈₎ A2 ₍₀₋₈₎	Side A2 Inputs or TRI-STATE Outputs
B2 ₍₀₋₈₎	Side B2 Inputs or TRI-STATE Outputs
<u>G1, G2</u>	Output Enable Pins (Active Low)
DIR1, DIR2	Direction of Data Flow Pins

Order Number	Description
SCAN182245ASSC	SSOP in Tubes
SCAN182245ASSCX	SSOP Tape and Reel
SCAN182245AFMQB	Flatpak Military

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Truth Tables

Inp	outs	A1 ₍₀₋₈₎	B1 ₍₀₋₈₎
† <mark>G1</mark>	DIR1	A '(0-8)	0-8)
L	L	Н ←	— н
L	L	L +	– L
L	н	н –	→ Н
L	н	L –	→ L
Н	Х	Z	Z

Inp	outs	A2 ₍₀₋₈₎	B2/0 0
† G2	DIR2	72(0-8)	B2 ₍₀₋₈₎
L	L	Н ←	— н
L	L	L ←	– L
L	н	н –	→ Н
L	н	L -	→ L
н	Х	Z	Z

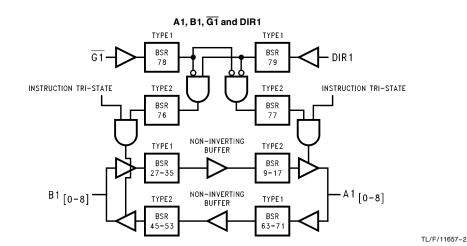
Functional Description

The SCAN182245A consists of two sets of nine non-inverting bidirectional buffers with TRI-STATE outputs and is intended for bus-oriented applications. Direction pins (DIR1 and DIR2) LOW enables data from B ports to A ports, when HIGH enables data from A ports to B ports. The Output Enable pins ($\overline{G1}$ and $\overline{G2}$) when HIGH disables both A and B ports by placing them in a high impedance condition.

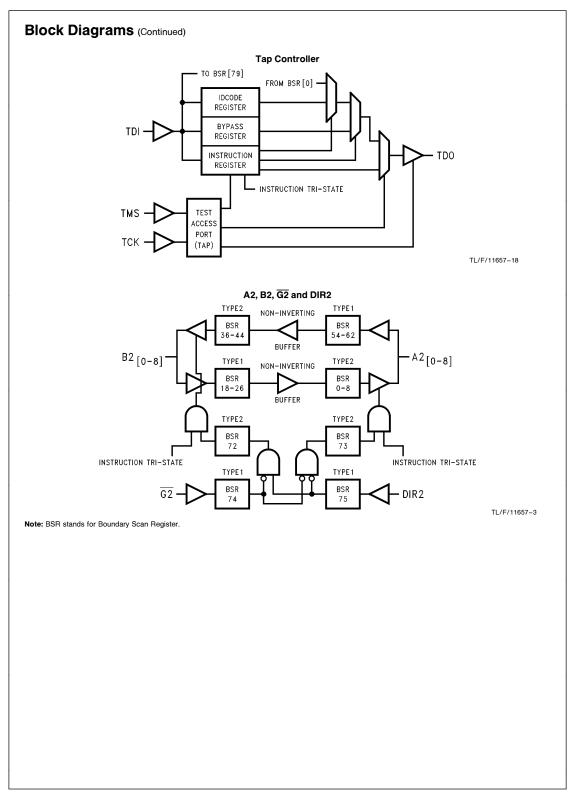
Z = Immaterial Z = High Impedance † = Inactive-to-Active transition must occur to enable outputs upon **Block Diagrams**

L

H = HIGH Voltage Level = LOW Voltage Level



Note: BSR stands for Boundary Scan Register.



Description of BOUNDARY-SCAN Circuitry

The scan cells used in the BOUNDARY-SCAN register are one of the following two types depending upon their location. Scan cell TYPE1 is intended to solely observe system data, while TYPE2 has the additional ability to control system data. (See IEEE Standard 1149.1 Figure 10-11 for a further description of scan cell TYPE1 and Figure 10-12 for a further description of scan cell TYPE2.)

Scan cell TYPE1 is located on each system input pin while scan cell TYPE2 is located at each system output pin as well as at each of the two internal active-high output enable signals. AOE controls the activity of the A-outputs while BOE controls the activity of the B-outputs. Each will activate their respective outputs by loading a logic high.

The BYPASS register is a single bit shift register stage identical to scan cell TYPE1. It captures a fixed logic low.

Bypass Register Scan Chain Definition



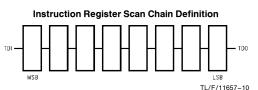
TL/F/11657-17

SCAN182245A Product IDCODE (32-Bit Code per IEEE 1149.1)

Version	Entity	Part Number	Manufacturer ID	Required by 1149.1	
0000	111111	0000000000	00000001111	1	
MSB				LSB	

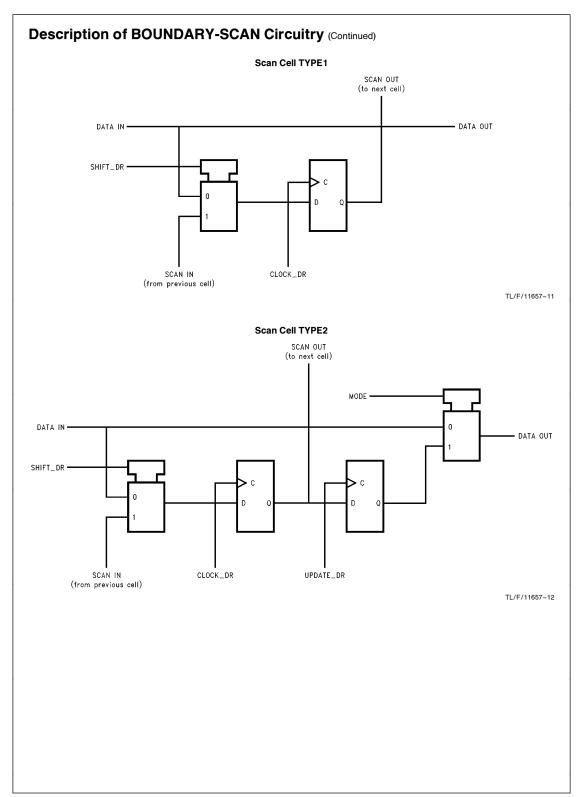
MSE

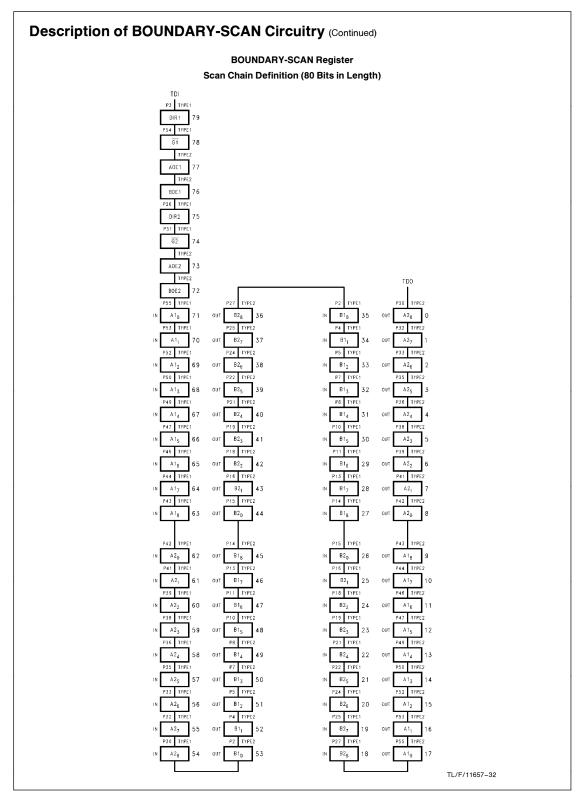
The INSTRUCTION register is an 8-bit register which captures the default value of 10000001 (SAMPLE/PRELOAD) during the CAPTURE-IR instruction command. The benefit of capturing SAMPLE/PRELOAD as the default instruction during CAPTURE-IR is that the user is no longer required to shift in the 8-bit instruction for SAMPLE/PRELOAD. The sequence of: CAPTURE-IR \rightarrow EXIT1-IR \rightarrow UPDATE-IR will update the SAMPLE/PRELOAD instruction. For more information refer to the section on instruction definitions.



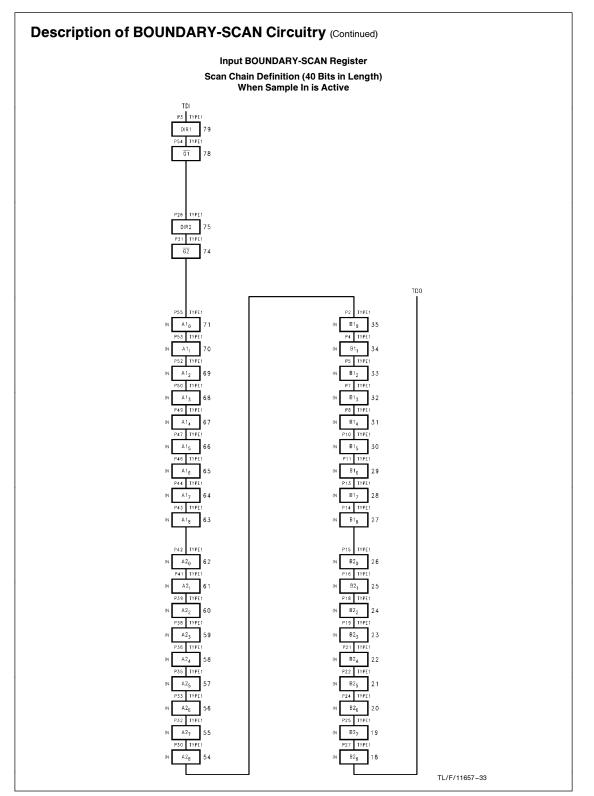
 $MSB \rightarrow LSB$

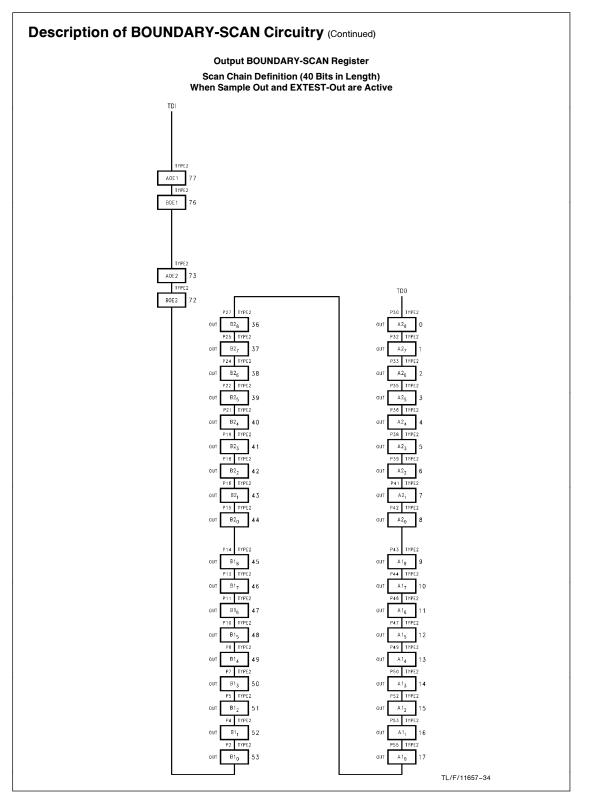
MOD · LOD						
Instruction Code	Instruction					
00000000	EXTEST					
1000001	SAMPLE/PRELOAD					
10000010	CLAMP					
00000011	HIGH-Z					
01000001	SAMPLE-IN					
01000010	SAMPLE-OUT					
00100010	EXTEST-OUT					
10101010	IDCODE					
1111111	BYPASS					
All Others	BYPASS					





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	B	JUNDARY-SCAN Reg	gister Definition Index		
Bit No.	Pin Name	Pin No.	Pin Type	Scan C	ell Type
79	DIR1	3	Input	TYPE1	
78	G1	54	Input	TYPE1	
77	AOE1		Internal	TYPE2	
76	BOE ₁		Internal	TYPE2	Control
75	DIR2	26	Input	TYPE1	Signals
74	$\frac{\overline{G2}}{\overline{G2}}$	31		TYPE1	eignaid
		51	Input		
73 70	AOE ₂		Internal	TYPE2	
72	BOE ₂		Internal	TYPE2	
71	A10	55	Input	TYPE1	
70	A1 ₁	53	Input	TYPE1	
69	A12	52	Input	TYPE1	
68	A1 ₃	50	Input	TYPE1	
67	A14	49	Input	TYPE1	A1-in
66	A15	47	Input	TYPE1	
65	A16	46	Input	TYPE1	
64	A17	44	Input	TYPE1	
63	A1 ₈	43	Input	TYPE1	
62	A20	42	Input	TYPE1	
61	A21	41	Input	TYPE1	
60	A22	39	Input	TYPE1	
59	A23	38	Input	TYPE1	
	-	36			A2-in
58	A24		Input	TYPE1	A2-11
57	A25	35	Input	TYPE1	
56	A2 ₆	33	Input	TYPE1	
55	A2 ₇	32	Input	TYPE1	
54	A2 ₈	30	Input	TYPE1	
53	B1 ₀	2	Output	TYPE2	
52	B1 ₁	4	Output	TYPE2	
51	B12	5	Output	TYPE2	
50	B13	7	Output	TYPE2	
49	B14	8	Output	TYPE2	B1-out
48	B15	10	Output	TYPE2	
47	B1 ₆	11	Output	TYPE2	
46	B17	13	Output	TYPE2	
45	B1 ₈	14	Output	TYPE2	
44	B20	15	Output	TYPE2	
44 43	B20 B21	16	Output	TYPE2	
43 42	B2 ₂	18	Output	TYPE2	
	_				
41	B23	19	Output	TYPE2	
40	B24	21	Output	TYPE2	B2-out
39	B25	22	Output	TYPE2	
38	B2 ₆	24	Output	TYPE2	
37	B27	25	Output	TYPE2	
36	B2 ₈	27	Output	TYPE2	
35	B1 ₀	2	Input	TYPE1	
34	B1 ₁	4	Input	TYPE1	
33	B12	5	Input	TYPE1	
32	B1 ₃	7	Input	TYPE1	
31	B14	8	Input	TYPE1	B1-in
30	B15	10	Input	TYPE1	
29	B1 ₆	11	Input	TYPE1	
28	B17	13	Input	TYPE1	
27	B1 ₈	14	Input	TYPE1	

Bit No.	Pin Name	Pin No.	Pin Type	Scan C	ell Type
26	B20	15	Input	TYPE1	
25	B21	16	Input	TYPE1	
24	B2 ₂	18	Input	TYPE1	
23	B23	19	Input	TYPE1	
22	B24	21	Input	TYPE1	B2-in
21	B25	22	Input	TYPE1	
20	B2 ₆	24	Input	TYPE1	
19	B27	25	Input	TYPE1	
18	B2 ₈	27	Input	TYPE1	
17	A1 ₀	55	Output	TYPE2	
16	A1 ₁	53	Output	TYPE2	
15	A1 ₂	52	Output	TYPE2	
14	A13	50	Output	TYPE2	
13	A14	49	Output	TYPE2	A1-out
12	A1 ₅	47	Output	TYPE2	
11	A16	46	Output	TYPE2	
10	A17	44	Output	TYPE2	
9	A1 ₈	43	Output	TYPE2	
8	A20	42	Output	TYPE2	
7	A2 ₁	41	Output	TYPE2	
6	A22	39	Output	TYPE2	
5	A23	38	Output	TYPE2	
4	A24	36	Output	TYPE2	A2-out
3	A25	35	Output	TYPE2	
2	A2 ₆	33	Output	TYPE2	
1 0	A2 ₇ A2 ₈	32 30	Output Output	TYPE2 TYPE2	

SCAN ABT Live Insertion and Power Cycling Characteristics

SCAN ABT is intended to serve in Live Insertion backplane applications. It provides 2nd Level Isolation¹ which indicates that while external circuitry to control the output enable pin is unnecessary, there may be a need to implement differential length backplane connector pins for V_{CC} and GND. As well, pre-bias circuitry for backplane pins may be necessary to avoid capacitive loading effects during live insertion.

SCAN ABT provides control of output enable pins during power cycling via the circuit in *Figure A*. It essentially controls the $\overline{G_n}$ pin until V_{CC} reaches a known level.

During *power-up*, when V_{CC} ramps through the 0.0V to 0.7V range, all internal device circuitry is inactive, leaving output and I/O pins of the device in high impedance. From approximately 0.8V to 1.8V V_{CC}, the Power-On-Reset circuitry, (POR), in *Figure A* becomes active and maintains device high impedance mode. The POR does this by providing a low from its output that resets the flip-flop The output, \overline{Q} , of the flip-flop then goes high and disables the NOR gate from an incidental low input on the $\overline{G_n}$ pin. After 1.8V V_{CC}, the POR circuitry becomes inactive and ceases to control the

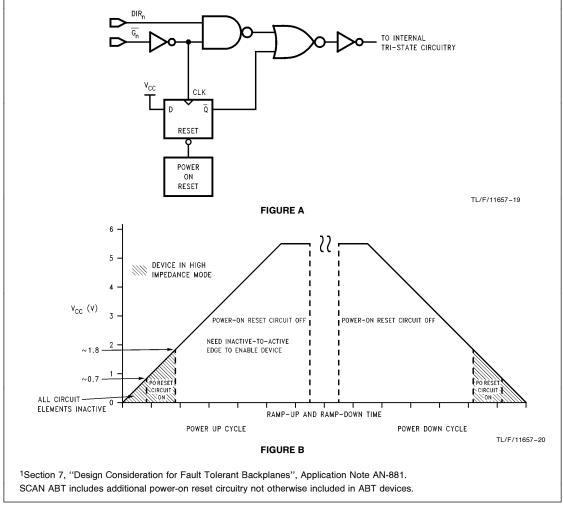
flip-flop. To bring the device out of high impedance, the $\overline{G_n}$ input must receive an inactive-to-active transition, a high-to-low transition on $\overline{G_n}$ in this case to change the state of the flip-flop. With a low on the \overline{Q} output of the flip-flop, the NOR gate is free to allow propagation of a $\overline{G_n}$ signal.

During *power-down*, the Power-On-Reset circuitry will become active and reset the flip-flop at approximately 1.8V V_{CC}. Again, the \overline{Q} output of the flip-flop returns to a high and disables the NOR gate from inputs from the $\overline{G_n}$ pin. The device will then remain in high impedance for the remaining ramp down from 1.8V to 0.0V V_{CC}.

Some suggestions to help the designer with live insertion issues:

- The Gn pin can float during power-up until the Power-On-Reset circuitry becomes inactive.
- The $\overline{G_n}$ pin can float on power-down only after the Power-On-Reset has become active.

The description of the functionality of the Power-On-Reset circuitry can best be described in the diagram of *Figure B*.



Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature	-65°C to +150°C
Ambient Temperature under Bias	-55°C to +125°C
Junction Temperature under Bias	i
Ceramic	-55°C to +175°C
Plastic	-55°C to +150°C
V _{CC} Pin Potential to	
Ground Pin	-0.5V to +7.0V
Input Voltage (Note 2)	-0.5V to $+7.0V$
Input Current (Note 2)	-30 mA to $+5.0$ mA
Voltage Applied to Any Output	
in the Disabled or	
Power-Off State	-0.5V to +5.5V
in the HIGH State	-0.5V to V _{CC}
Current Applied to Output	
in LOW State (Max)	Twice the Rated I _{OL} (mA)

DC Latchup Source Current	
Commercial	-500 mA
Military	-300 mA
Over Voltage Latchup (I/O)	10V
ESD (HBM) Min.	2000V
Note 1: Absolute maximum ratings are values beyond w be damaged or have its useful life impaired. Function these conditions is not implied.	,
Note 2: Either voltage limit or current limit is sufficient	to protect inputs.

Recommended Operating Conditions

	• •				-			

Free Air Ambient Temperature	
Military	-55°C to +125°C
Commercial	-40°C to +85°C
Supply Voltage	
Military	+4.5V to +5.5V
Commercial	+4.5V to +5.5V
Minimum Input Edge Rate	$(\Delta V / \Delta t)$
Data Input	50 mV/ns
Enable Input	20 mV/ns

DC Electrical Characteristics

Symbol	Parameter	•	Vcc	Min	Тур	Мах	Units	Conditions
V _{IH}	Input HIGH Voltage			2.0			V	Recognized HIGH Signa
VIL	Input LOW Voltage					0.8	V	Recognized LOW Signal
V _{CD}	Input Clamp Diode Voltage		Min			-1.2	V	$I_{IN} = -18 \text{ mA}$
V _{OH}	Output HIGH Voltage		Min	2.5			V	$I_{OH} = -3 \text{ mA}$
		Mil	Min	2.0			V	$I_{OH} = -24 \text{ mA}$
		Comm	Min	2.0			V	$I_{OH} = -32 \text{ mA}$
V _{OL}	Output LOW Voltage	Mil	Min			0.8	v	$I_{OL} = 12 \text{ mA}$
		Comm	Min			0.8	V	$I_{OL} = 15 \text{ mA}$
IIH	Input HIGH Current	All Others	Max			5	μΑ	V _{IN} = 2.7V (Note 1)
		All Others	Max			5	μA	$V_{IN} = V_{CC}$
		TMS, TDI	Max			5	μΑ	$V_{IN} = V_{CC}$
I _{BVI}	Input HIGH Current Breakdown Test		Мах			7	μΑ	$V_{IN} = 7.0V$
I _{BVIT}	Input HIGH Current Breakdown Test (I/O)		Max			100	μΑ	$V_{IN} = 5.5V$
IIL	Input LOW Current	All Others	Max			-5	μA	V _{IN} = 0.5V (Note 1)
		All Others	Max			-5	μA	$V_{IN} = 0.0V$
		TMS, TDI	Max			-385	μA	$V_{IN} = 0.0V$
V _{ID}	Input Leakage Test		0.0	4.75			v	$I_{ID} = 1.9 \mu A$ All Other Pins Grounded
I _{IH} + I _{OZH}	Output Leakage Current	t	Max			50	μΑ	$V_{OUT} = 2.7V$
$I_{IL} + I_{OZL}$	Output Leakage Current	t	Max			-50	μA	$V_{OUT} = 0.5V$
I _{OZH}	Output Leakage Current	t	Max			50	μΑ	$V_{OUT} = 2.7V$
I _{OZL}	Output Leakage Current	t	Max		-	-50	μA	$V_{OUT} = 0.5V$

Symbol	Parameter	V _{CC}	Min	Тур	Max	Units	Conditions
I _{OS}	Output Short-Circuit Current	Max	-100		-275	mA	$V_{OUT} = 0.0V$
ICEX	Output HIGH Leakage Current	Max			50	μΑ	$V_{OUT} = V_{CC}$
I _{ZZ}	Bus Drainage Test	0.0			100	μΑ	V _{OUT} = 5.5V All Others GND
ICCH	Power Supply Current	Max			250	μA	$V_{OUT} = V_{CC}$; TDI, TMS = V_{CC}
		Мах			1.0	mA	$V_{OUT} = V_{CC}$; TDI, TMS = GND
I _{CCL}	Power Supply Current	Max			65	mA	$V_{OUT} = LOW; TDI, TMS = V_{CC}$
		Max			65.8	mA	$V_{OUT} = LOW; TDI, TMS = GNE$
Iccz	Power Supply Current	Max			250	μΑ	TDI, TMS = V_{CC}
		Max			1.0	mA	TDI, TMS = GND
ICCT	Additional I _{CC} /Input All Other Inputs	Max			2.9	mA	$V_{IN} = V_{CC} - 2.1V$
	TDI, TMS inputs	Max			3	mA	$V_{IN} = V_{CC} - 2.1V$
ICCD	Dynamic I _{CC} No Load	Max			0.2	mA/ MHz	Outputs Open One Bit Toggling, 50% Duty Cyc

AC Electrical Characteristics Normal Operation

Symbol	Parameter	V _{CC} * (V)	T _A =	$\label{eq:TA} \begin{split} & \mbox{Military} \\ & \mbox{T}_{\mbox{A}} = -55^{\circ}\mbox{C to} + 125^{\circ}\mbox{C} \\ & \mbox{C}_{\mbox{L}} = 50\mbox{ pF} \end{split}$			Commercial = -40°C to + C _L = 50 pF		Units
			Min	Тур	Max	Min	Тур	Мах	
t _{PLH} t _{PHL}	Propagation Delay A to B, B to A	5.0				1.0 1.5	3.1 4.4	5.2 6.5	ns
t _{PLZ} t _{PHZ}	Disable Time	5.0				1.5 1.5	4.8 5.2	8.6 8.9	ns
t _{PZL} t _{PZH}	Enable Time	5.0				1.5 1.5	5.5 4.6	9.1 8.2	ns

*Voltage Range 5.0V $\pm 0.5V$

				Military			Commercial		
Symbol	Parameter	V _{CC} * (V)		55°C to + _L = 50 pF	125°C	T _A =	85°C	Units	
			Min	Тур	Мах	Min	Тур	Мах	
t _{PLH} t _{PHL}	Propagation Delay TCK to TDO	5.0				2.9 4.2	6.1 7.7	10.2 12.1	ns
t _{PLZ} t _{PHZ}	Disable Time TCK to TDO	5.0				2.1 3.3	5.9 7.4	10.7 12.5	ns
t _{PZL} t _{PZH}	Enable Time TCK to TDO	5.0				4.6 2.8	8.7 6.8	13.7 11.5	ns
t _{PLH} t _{PHL}	Propagation Delay TCK to Data Out during Update-DR State	5.0				2.8 4.5	6.3 8.2	10.7 13.0	ns
t _{PLH} t _{PHL}	Propagation Delay TCK to Data Out during Update-IR State	5.0				3.3 5.0	7.2 9.3	12.2 14.8	ns
t _{PLH} t _{PHL}	Propagation Delay TCK to Data Out during Test Logic Reset State	5.0				3.7 5.7	8.4 10.8	14.0 17.2	ns
t _{PLZ} t _{PHZ}	Disable Time TCK to Data Out during Update-DR State	5.0				2.8 3.5	7.6 8.4	13.9 14.5	ns
t _{PLZ} t _{PHZ}	Disable Time TCK to Data Out during Update-IR State	5.0				3.6 3.8	8.7 9.2	15.1 15.9	ns
t _{PLZ} t _{PHZ}	Disable Time TCK to Data Out during Test Logic Reset State	5.0				4.0 4.2	9.8 9.9	17.1 16.6	ns
t _{PZL} t _{PZH}	Enable Time TCK to Data Out during Update-DR State	5.0				4.4 3.0	9.3 7.5	15.5 13.3	ns
t _{PZL} t _{PZH}	Enable Time TCK to Data Out during Update-IR State	5.0				5.2 3.9	10.7 9.0	17.4 15.4	ns
t _{PZL} t _{PZH}	Enable Time TCK to Data Out during Test Logic Reset State	5.0				5.7 3.0	12.0 10.2	19.8 17.6	ns

*Voltage Range 5.0V $\pm 0.5V$

All Propagation Delays involving TCK are measured from the falling edge of TCK.

			Military	Commercial	Units
Symbol	Parameter	V _{CC} * (V)	$\label{eq:T_A} \begin{split} \mathbf{T}_{\mathbf{A}} &= -55^\circ \mathbf{C} \ \mathbf{to} \ + 125^\circ \mathbf{C} \\ \mathbf{C}_{\mathbf{L}} &= 50 \ \mathbf{pF} \end{split}$	${f T_A}=-40^\circ{f C}$ to $+85^\circ{f C}$ ${f C_L}=50$ pF	
			Guaranteed	d Minimum	
ts	Setup Time Data to TCK (Note 1)	5.0		4.8	ns
t _H	Hold Time Data to TCK (Note 1)	5.0		2.5	ns
ts	Setup Time, H or L G1, G2 to TCK (Note 2)	5.0		4.1	ns
t _H	Hold Time, H or L TCK to G1, G2 (Note 2)	5.0		1.7	ns
ts	Setup Time, H or L DIR1, DIR2 to TCK (Note 4)	5.0		4.2	ns
t _H	Hold Time, H or L TCK to DIR1, DIR2 (Note 4)	5.0		2.3	ns
ts	Setup Time Internal OE to TCK (Note 3)	5.0		3.8	ns
t _H	Hold Time, H or L TCK to Internal OE (Note 3)	5.0		2.3	ns
ts	Setup Time, H or L TMS to TCK	5.0		8.7	ns
t _H	Hold Time, H or L TCK to TMS	5.0		1.5	ns
ts	Setup Time, H or L TDI to TCK	5.0		6.7	ns
t _H	Hold Time, H or L TCK to TDI	5.0		5.0	ns
t _W	Pulse Width TCK H	5.0		10.2 8.5	ns
f _{max}	Maximum TCK Clock Frequency	5.0		50	MHz
t _{PU}	Wait Time, Power Up to TCK	5.0		100	ns
t _{DN}	Power Down Delay	0.0		100	ms

All Input Timing Delays involving TCK are measured from the rising edge of TCK.

Note 1: Timing pertains to the TYPE1 BSR and TYPE2 BSR after the buffer (BSR 0-8, 9-17, 18-26, 27-35, 36-44, 45-53, 54-62, 63-71).

Note 2: Timing pertains to BSR 74 and 78 only.

Note 3: Timing pertains to BSR 72, 73, 76 and 77 only.

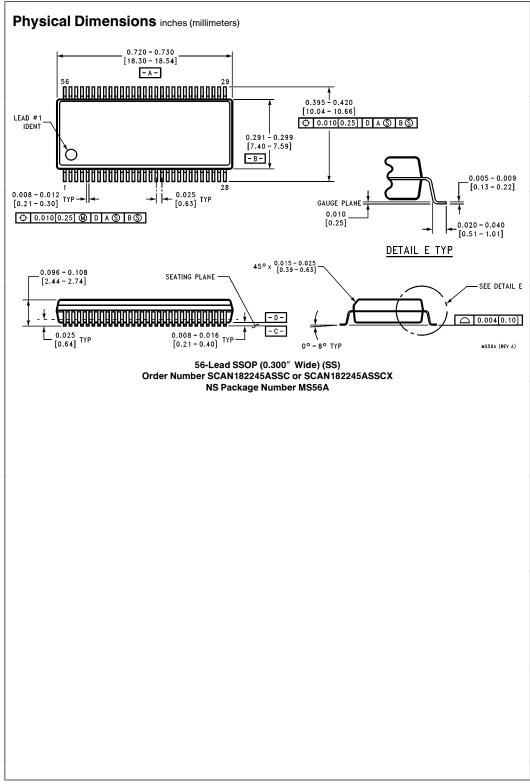
Note 4: Timing pertains to BSR 75 and 79 only.

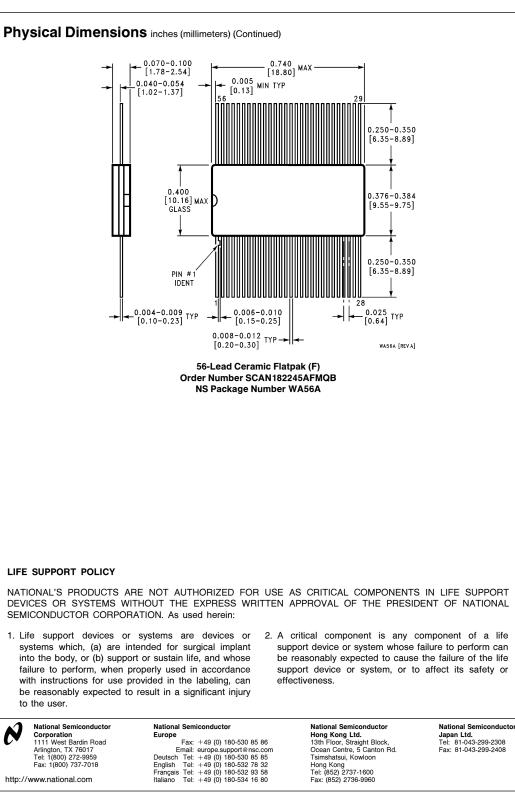
Capacitance

Symbol	Parameter	Тур	Units	Conditions, $T_A = 25^{\circ}C$
C _{IN}	Input Capacitance	5.9	pF	$V_{CC} = 0.0V (\overline{G}_n, DIR_n)$
CI/O (Note 1)	Output Capacitance	13.7	pF	$V_{CC} = 5.0V (A_n, B_n)$

Note 1: $C_{I/O}$ is measured at frequency f = 1 MHz, per MIL-STD-883B, Method 3012.

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erially Controlled Access Network ————— 8-Bit Logic ————————————————————————————————————						Special Variations X = Tape and Reel QB = Military grade device with environmental and burn-in processing.
echnology Designator T = TTL Input TTL Output CMOS Device C = CMOS Input/Output CMOS Device B = Bipolar TTL Device E = ECL Device A = BiCMOS Device						Temperature Range C = Commercial (-40°C to +85°C) M = Military (-55°C to +125°C)
F = TTL Input/CMOS Output CMOS Devic	e					Package Code SS = 25 mil Pitch (JEDEC) SSOP F = 25 mil Pitch Ceramic Flatpak





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